

# Santosh Kumar Gupta

## List of Publications by Year in descending order

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14  
papers

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citations

1307594

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1199594

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docs citations

16  
times ranked

76  
citing authors

#	ARTICLE	IF	CITATIONS
1	Linearity Distortion Analysis of Junctionless Quadruple Gate MOSFETs for Analog Applications. Silicon, 2019, 11, 257-265.	3.3	33
2	Threshold voltage model of junctionless cylindrical surrounding gate MOSFETs including fringing field effects. Superlattices and Microstructures, 2015, 88, 188-197.	3.1	21
3	Potential modeling and performance analysis of junction-less quadruple gate MOSFETs for analog and RF applications. Microelectronics Journal, 2017, 66, 89-102.	2.0	18
4	EMA-based modeling of the surface potential and drain current of dual-material gate-all-around TFETs. Journal of Computational Electronics, 2018, 17, 1596-1602.	2.5	18
5	Analytical modelling and electrical characterisation of ZnO based HEMTs. International Journal of Electronics, 2019, 106, 707-720.	1.4	15
6	Analog/RF and Linearity Distortion Analysis of MgZnO/CdZnO Quadruple-Gate Field Effect Transistor (QG-FET). Silicon, 2021, 13, 91-107.	3.3	13
7	A charge-plasma-based dual-metal-gate recessed-source/drain dopingless junctionless transistor with enhanced analog and RF performance. Journal of Computational Electronics, 2020, 19, 1085-1099.	2.5	9
8	Center Potential Based Analysis of Si and III-V Gate all around Field Effect Transistors (GAA-FETs). Silicon, 2021, 13, 1787-1803.	3.3	8
9	Al embedded MgO barrier MTJ: A first principle study for application in fast and compact STT-MRAMs. Superlattices and Microstructures, 2017, 103, 314-324.	3.1	5
10	A comparative first principles study of quantum well states in MgO barrier MTJs for STT-RAMs. Microelectronics Journal, 2020, 105, 104909.	2.0	5
11	Comparative Analysis of Different Figures of Merit for AlGaIn/GaN and Si Surrounding-Gate Field Effect Transistors (SG-FETs). Silicon, 2022, 14, 3027-3036.	3.3	4
12	Performance Enhancement of AlGaIn/GaN HEMT by Optimization of Device Parameters Considering Nanometer Barrier Layer Thickness. International Journal of Nanoscience, 2020, 19, 2050011.	0.7	2
13	FeAl/MgO/FeAl MTJ with enhanced TMR and low resistance area product for MRAM: A first principle study. , 2022, 165, 207192.		2
14	Performance of Double Gate Tunnel FET Devices with Source Pocket. Lecture Notes in Electrical Engineering, 2020, , 387-395.	0.4	1